



Welcome to [E-XFL.COM](#)

Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details

Product Status	Obsolete
Number of LABs/CLBs	832
Number of Logic Elements/Cells	8320
Total RAM Bits	106496
Number of I/O	382
Number of Gates	526000
Voltage - Supply	2.375V ~ 2.625V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	484-BBGA
Supplier Device Package	484-FBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep20k200fi484-3

Each LE has two outputs that drive the local, MegaLAB, or FastTrack Interconnect routing structure. Each output can be driven independently by the LUT's or register's output. For example, the LUT can drive one output while the register drives the other output. This feature, called register packing, improves device utilization because the register and the LUT can be used for unrelated functions. The LE can also drive out registered and unregistered versions of the LUT output.

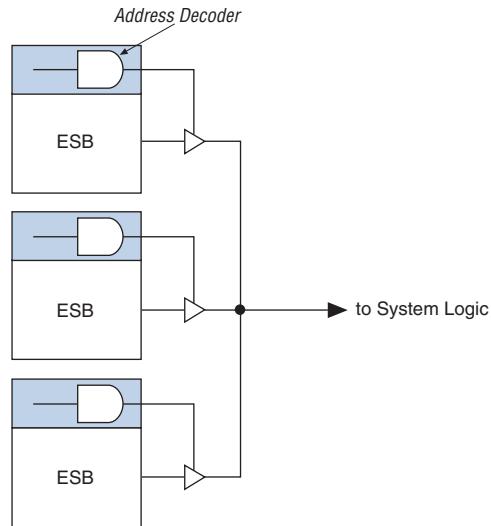
The APEX 20K architecture provides two types of dedicated high-speed data paths that connect adjacent LEs without using local interconnect paths: carry chains and cascade chains. A carry chain supports high-speed arithmetic functions such as counters and adders, while a cascade chain implements wide-input functions such as equality comparators with minimum delay. Carry and cascade chains connect LEs 1 through 10 in an LAB and all LABs in the same MegaLAB structure.

Carry Chain

The carry chain provides a very fast carry-forward function between LEs. The carry-in signal from a lower-order bit drives forward into the higher-order bit via the carry chain, and feeds into both the LUT and the next portion of the carry chain. This feature allows the APEX 20K architecture to implement high-speed counters, adders, and comparators of arbitrary width. Carry chain logic can be created automatically by the Quartus II software Compiler during design processing, or manually by the designer during design entry. Parameterized functions such as library of parameterized modules (LPM) and DesignWare functions automatically take advantage of carry chains for the appropriate functions.

The Quartus II software Compiler creates carry chains longer than ten LEs by linking LABs together automatically. For enhanced fitting, a long carry chain skips alternate LABs in a MegaLAB™ structure. A carry chain longer than one LAB skips either from an even-numbered LAB to the next even-numbered LAB, or from an odd-numbered LAB to the next odd-numbered LAB. For example, the last LE of the first LAB in the upper-left MegaLAB structure carries to the first LE of the third LAB in the MegaLAB structure.

Figure 6 shows how an n -bit full adder can be implemented in $n + 1$ LEs with the carry chain. One portion of the LUT generates the sum of two bits using the input signals and the carry-in signal; the sum is routed to the output of the LE. The register can be bypassed for simple adders or used for accumulator functions. Another portion of the LUT and the carry chain logic generates the carry-out signal, which is routed directly to the carry-in signal of the next-higher-order bit. The final carry-out signal is routed to an LE, where it is driven onto the local, MegaLAB, or FastTrack Interconnect routing structures.

Figure 18. Deep Memory Block Implemented with Multiple ESBs

The ESB implements two forms of dual-port memory: read/write clock mode and input/output clock mode. The ESB can also be used for bidirectional, dual-port memory applications in which two ports read or write simultaneously. To implement this type of dual-port memory, two or four ESBs are used to support two simultaneous reads or writes. This functionality is shown in [Figure 19](#).

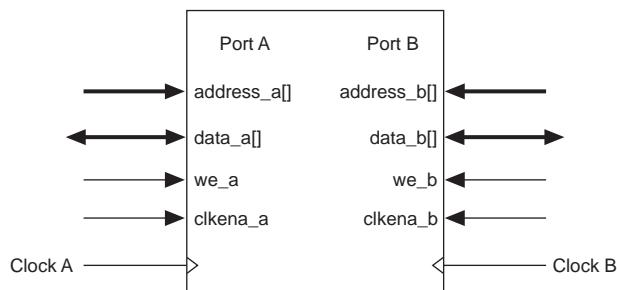
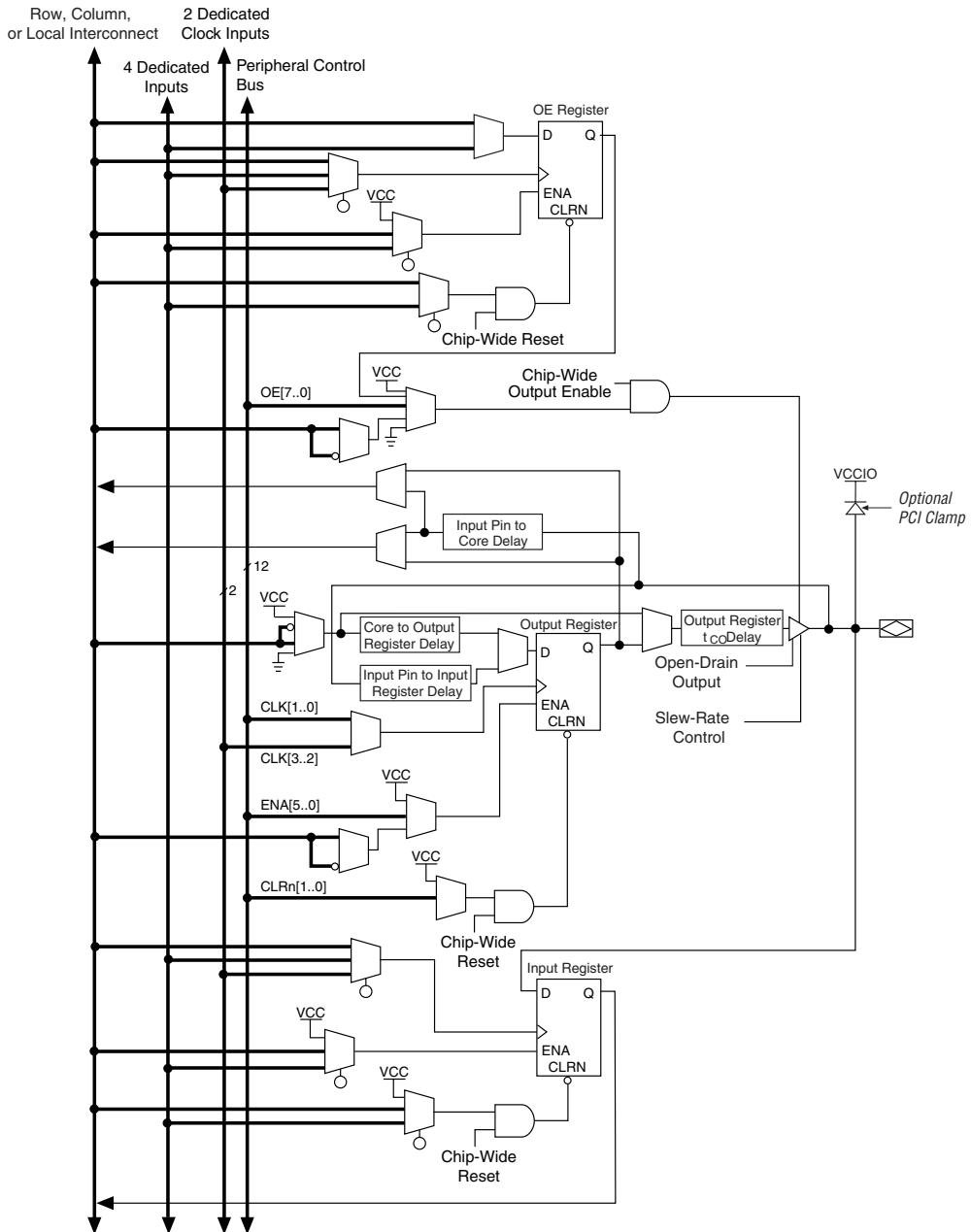
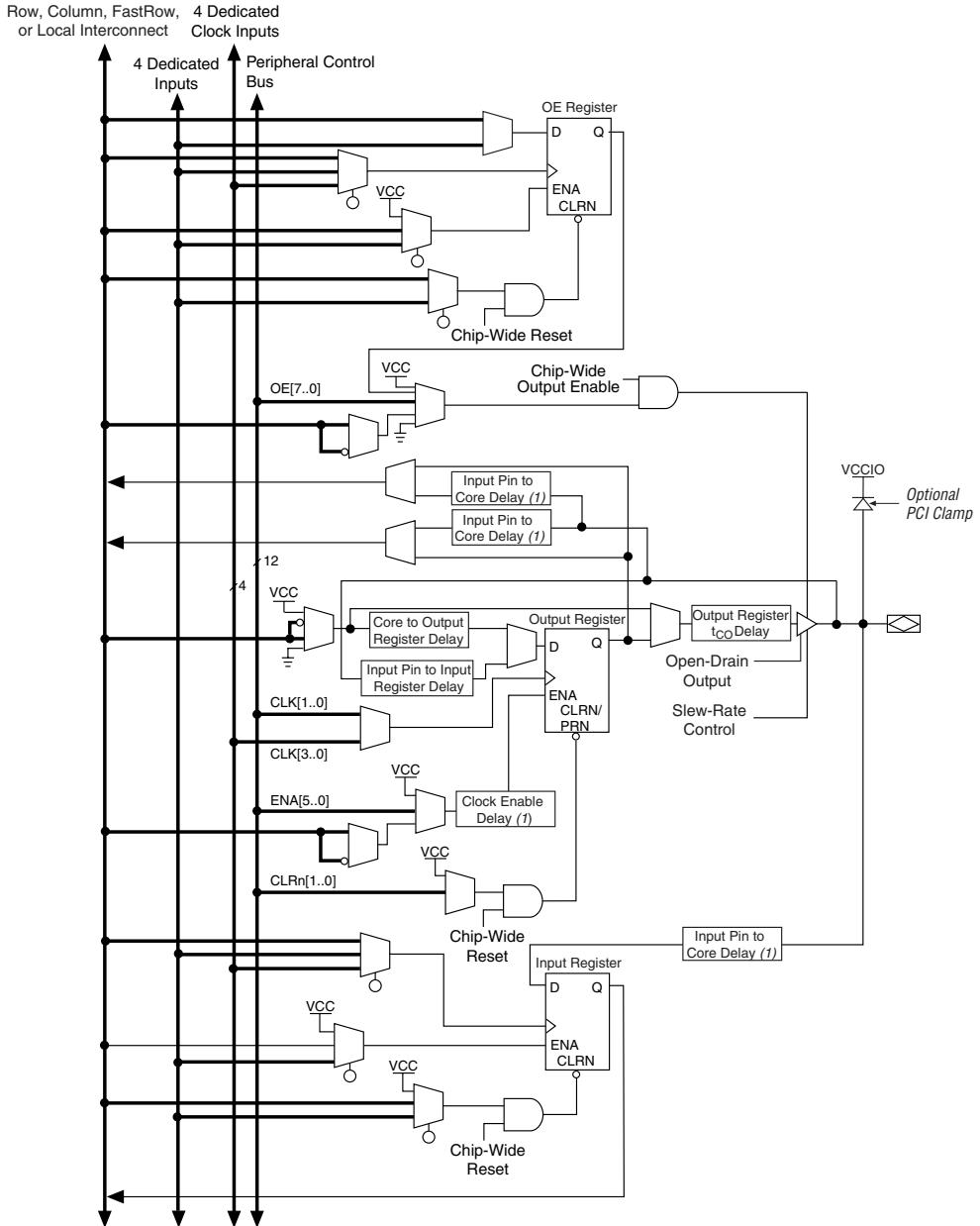
Figure 19. APEX 20K ESB Implementing Dual-Port RAM

Figure 25. APEX 20K Bidirectional I/O Registers Note (1)**Note to Figure 25:**

- (1) The output enable and input registers are LE registers in the LAB adjacent to the bidirectional pin.

Figure 26. APEX 20KE Bidirectional I/O Registers Notes (1), (2)**Notes to Figure 26:**

- (1) This programmable delay has four settings: off and three levels of delay.
- (2) The output enable and input registers are LE registers in the LAB adjacent to the bidirectional pin.

The APEX 20K device instruction register length is 10 bits. The APEX 20K device USERCODE register length is 32 bits. [Tables 20](#) and [21](#) show the boundary-scan register length and device IDCODE information for APEX 20K devices.

Table 20. APEX 20K Boundary-Scan Register Length

Device	Boundary-Scan Register Length
EP20K30E	420
EP20K60E	624
EP20K100	786
EP20K100E	774
EP20K160E	984
EP20K200	1,176
EP20K200E	1,164
EP20K300E	1,266
EP20K400	1,536
EP20K400E	1,506
EP20K600E	1,806
EP20K1000E	2,190
EP20K1500E	1 (1)

Note to Table 20:

- (1) This device does not support JTAG boundary scan testing.

Table 21. 32-Bit APEX 20K Device IDCODE

Device	IDCODE (32 Bits) (1)			
	Version (4 Bits)	Part Number (16 Bits)	Manufacturer Identity (11 Bits)	1 (1 Bit) (2)
EP20K30E	0000	1000 0000 0011 0000	000 0110 1110	1
EP20K60E	0000	1000 0000 0110 0000	000 0110 1110	1
EP20K100	0000	0000 0100 0001 0110	000 0110 1110	1
EP20K100E	0000	1000 0001 0000 0000	000 0110 1110	1
EP20K160E	0000	1000 0001 0110 0000	000 0110 1110	1
EP20K200	0000	0000 1000 0011 0010	000 0110 1110	1
EP20K200E	0000	1000 0010 0000 0000	000 0110 1110	1
EP20K300E	0000	1000 0011 0000 0000	000 0110 1110	1
EP20K400	0000	0001 0110 0110 0100	000 0110 1110	1
EP20K400E	0000	1000 0100 0000 0000	000 0110 1110	1
EP20K600E	0000	1000 0110 0000 0000	000 0110 1110	1
EP20K1000E	0000	1001 0000 0000 0000	000 0110 1110	1

Notes to Table 21:

- (1) The most significant bit (MSB) is on the left.
- (2) The IDCODE's least significant bit (LSB) is always 1.

Figure 31 shows the timing requirements for the JTAG signals.

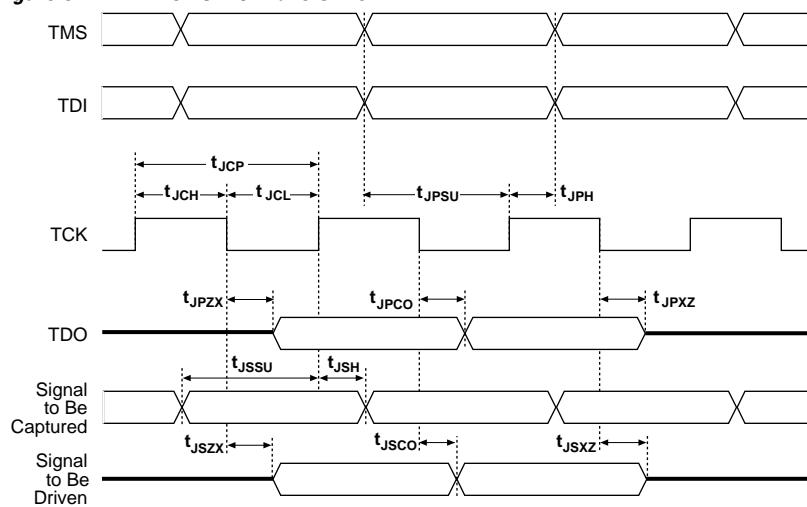
Figure 31. APEX 20K JTAG Waveforms

Table 24. APEX 20K 5.0-V Tolerant Device Recommended Operating Conditions Note (2)

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage for internal logic and input buffers	(4), (5)	2.375 (2.375)	2.625 (2.625)	V
V_{CCIO}	Supply voltage for output buffers, 3.3-V operation	(4), (5)	3.00 (3.00)	3.60 (3.60)	V
	Supply voltage for output buffers, 2.5-V operation	(4), (5)	2.375 (2.375)	2.625 (2.625)	V
V_I	Input voltage	(3), (6)	-0.5	5.75	V
V_O	Output voltage		0	V_{CCIO}	V
T_J	Junction temperature	For commercial use	0	85	°C
		For industrial use	-40	100	°C
t_R	Input rise time			40	ns
t_F	Input fall time			40	ns

Table 25. APEX 20K 5.0-V Tolerant Device DC Operating Conditions (Part 1 of 2) Notes (2), (7), (8)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IH}	High-level input voltage		1.7, 0.5 × V_{CCIO} (9)		5.75	V
V_{IL}	Low-level input voltage		-0.5		0.8, 0.3 × V_{CCIO} (9)	V
V_{OH}	3.3-V high-level TTL output voltage	$I_{OH} = -8 \text{ mA DC}$, $V_{CCIO} = 3.00 \text{ V}$ (10)	2.4			V
	3.3-V high-level CMOS output voltage	$I_{OH} = -0.1 \text{ mA DC}$, $V_{CCIO} = 3.00 \text{ V}$ (10)	$V_{CCIO} - 0.2$			V
	3.3-V high-level PCI output voltage	$I_{OH} = -0.5 \text{ mA DC}$, $V_{CCIO} = 3.00 \text{ to } 3.60 \text{ V}$ (10)	$0.9 \times V_{CCIO}$			V
	2.5-V high-level output voltage	$I_{OH} = -0.1 \text{ mA DC}$, $V_{CCIO} = 2.30 \text{ V}$ (10)	2.1			V
		$I_{OH} = -1 \text{ mA DC}$, $V_{CCIO} = 2.30 \text{ V}$ (10)	2.0			V
		$I_{OH} = -2 \text{ mA DC}$, $V_{CCIO} = 2.30 \text{ V}$ (10)	1.7			V

Table 25. APEX 20K 5.0-V Tolerant Device DC Operating Conditions (Part 2 of 2) Notes (2), (7), (8)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{OL}	3.3-V low-level TTL output voltage	$I_{OL} = 12 \text{ mA DC}$, $V_{CCIO} = 3.00 \text{ V}$ (11)			0.45	V
	3.3-V low-level CMOS output voltage	$I_{OL} = 0.1 \text{ mA DC}$, $V_{CCIO} = 3.00 \text{ V}$ (11)			0.2	V
	3.3-V low-level PCI output voltage	$I_{OL} = 1.5 \text{ mA DC}$, $V_{CCIO} = 3.00 \text{ to } 3.60 \text{ V}$ (11)			$0.1 \times V_{CCIO}$	V
	2.5-V low-level output voltage	$I_{OL} = 0.1 \text{ mA DC}$, $V_{CCIO} = 2.30 \text{ V}$ (11)			0.2	V
		$I_{OL} = 1 \text{ mA DC}$, $V_{CCIO} = 2.30 \text{ V}$ (11)			0.4	V
		$I_{OL} = 2 \text{ mA DC}$, $V_{CCIO} = 2.30 \text{ V}$ (11)			0.7	V
I_I	Input pin leakage current	$V_I = 5.75 \text{ to } -0.5 \text{ V}$	-10		10	μA
I_{IOZ}	Tri-stated I/O pin leakage current	$V_O = 5.75 \text{ to } -0.5 \text{ V}$	-10		10	μA
I_{CC0}	V _{CC} supply current (standby) (All ESBs in power-down mode)	$V_I = \text{ground, no load, no}$ toggling inputs, -1 speed grade (12)		10		mA
		$V_I = \text{ground, no load, no}$ toggling inputs, -2, -3 speed grades (12)		5		mA
R_{CONF}	Value of I/O pin pull-up resistor before and during configuration	$V_{CCIO} = 3.0 \text{ V}$ (13)	20		50	W
		$V_{CCIO} = 2.375 \text{ V}$ (13)	30		80	W



For DC Operating Specifications on APEX 20KE I/O standards, please refer to *Application Note 117 (Using Selectable I/O Standards in Altera Devices)*.

Table 30. APEX 20KE Device Capacitance Note (15)

Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	$V_{IN} = 0 \text{ V}, f = 1.0 \text{ MHz}$		8	pF
C_{INCLK}	Input capacitance on dedicated clock pin	$V_{IN} = 0 \text{ V}, f = 1.0 \text{ MHz}$		12	pF
C_{OUT}	Output capacitance	$V_{OUT} = 0 \text{ V}, f = 1.0 \text{ MHz}$		8	pF

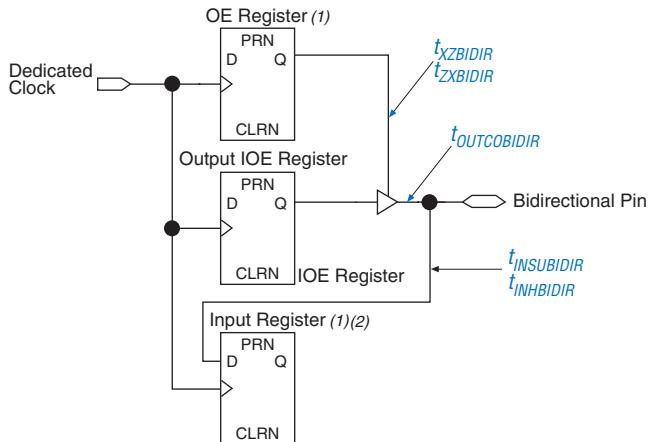
Notes to Tables 27 through 30:

- (1) See the *Operating Requirements for Altera Devices Data Sheet*.
- (2) Minimum DC input is -0.5 V . During transitions, the inputs may undershoot to -2.0 V or overshoot to 5.75 V for input currents less than 100 mA and periods shorter than 20 ns .
- (3) Numbers in parentheses are for industrial-temperature-range devices.
- (4) Maximum V_{CC} rise time is 100 ms , and V_{CC} must rise monotonically.
- (5) Minimum DC input is -0.5 V . During transitions, the inputs may undershoot to -2.0 V or overshoot to the voltage shown in the following table based on input duty cycle for input currents less than 100 mA . The overshoot is dependent upon duty cycle of the signal. The DC case is equivalent to 100% duty cycle.

V_{in}	Max. Duty Cycle
4.0V	100% (DC)
4.1	90%
4.2	50%
4.3	30%
4.4	17%
4.5	10%

- (6) All pins, including dedicated inputs, clock, I/O, and JTAG pins, may be driven before V_{CCINT} and V_{CCIO} are powered.
- (7) Typical values are for $T_A = 25^\circ \text{ C}$, $V_{CCINT} = 1.8 \text{ V}$, and $V_{CCIO} = 1.8 \text{ V}, 2.5 \text{ V}$ or 3.3 V .
- (8) These values are specified under the APEX 20KE device recommended operating conditions, shown in Table 24 on page 60.
- (9) Refer to *Application Note 117 (Using Selectable I/O Standards in Altera Devices)* for the V_{IH} , V_{IL} , V_{OH} , V_{OL} , and I_O parameters when $V_{CCIO} = 1.8 \text{ V}$.
- (10) The APEX 20KE input buffers are compatible with 1.8-V, 2.5-V and 3.3-V (LVTTL and LVCMOS) signals. Additionally, the input buffers are 3.3-V PCI compliant. Input buffers also meet specifications for GTL+, CTT, AGP, SSTL-2, SSTL-3, and HSTL.
- (11) The I_{OH} parameter refers to high-level TTL, PCI, or CMOS output current.
- (12) The I_{OL} parameter refers to low-level TTL, PCI, or CMOS output current. This parameter applies to open-drain pins as well as output pins.
- (13) This value is specified for normal device operation. The value may vary during power-up.
- (14) Pin pull-up resistance values will be lower if an external source drives the pin higher than V_{CCIO} .
- (15) Capacitance is sample-tested only.

Figure 33 shows the relationship between V_{CCIO} and V_{CCINT} for 3.3-V PCI compliance on APEX 20K devices.

Figure 40. Synchronous Bidirectional Pin External Timing**Notes to Figure 40:**

- (1) The output enable and input registers are LE registers in the LAB adjacent to a bidirectional row pin. The output enable register is set with “Output Enable Routing= Signal-Pin” option in the Quartus II software.
- (2) The LAB adjacent input register is set with “Decrease Input Delay to Internal Cells= Off”. This maintains a zero hold time for lab adjacent registers while giving a fast, position independent setup time. A faster setup time with zero hold time is possible by setting “Decrease Input Delay to Internal Cells= ON” and moving the input register farther away from the bidirectional pin. The exact position where zero hold occurs with the minimum setup time, varies with device density and speed grade.

Table 31 describes the f_{MAX} timing parameters shown in Figure 36 on page 68.

Table 31. APEX 20K f_{MAX} Timing Parameters (Part 1 of 2)

Symbol	Parameter
t_{SU}	LE register setup time before clock
t_H	LE register hold time after clock
t_{CO}	LE register clock-to-output delay
t_{LUT}	LUT delay for data-in
t_{ESBRC}	ESB Asynchronous read cycle time
t_{ESBWC}	ESB Asynchronous write cycle time
$t_{ESBWESU}$	ESB WE setup time before clock when using input register
$t_{ESBDATASU}$	ESB data setup time before clock when using input register
$t_{ESBDAWAH}$	ESB data hold time after clock when using input register
$t_{ESBADDRSU}$	ESB address setup time before clock when using input registers
$t_{ESBDAACO1}$	ESB clock-to-output delay when using output registers

Table 31. APEX 20K f_{MAX} Timing Parameters (Part 2 of 2)

Symbol	Parameter
$t_{ESBDA}CO_2$	ESB clock-to-output delay without output registers
t_{ESBDD}	ESB data-in to data-out delay for RAM mode
t_{PD}	ESB macrocell input to non-registered output
$t_{PTERMSU}$	ESB macrocell register setup time before clock
$t_{PTERMCO}$	ESB macrocell register clock-to-output delay
t_{F1-4}	Fanout delay using local interconnect
t_{F5-20}	Fanout delay using MegaLab Interconnect
t_{F20+}	Fanout delay using FastTrack Interconnect
t_{CH}	Minimum clock high time from clock pin
t_{CL}	Minimum clock low time from clock pin
t_{CLR}	LE clear pulse width
t_{PREP}	LE preset pulse width
t_{ESBCH}	Clock high time
t_{ESBCL}	Clock low time
t_{ESBWP}	Write pulse width
t_{ESBRP}	Read pulse width

Tables 32 and 33 describe APEX 20K external timing parameters.

Table 32. APEX 20K External Timing Parameters Note (1)

Symbol	Clock Parameter
t_{INSU}	Setup time with global clock at IOE register
t_{INH}	Hold time with global clock at IOE register
t_{OUTCO}	Clock-to-output delay with global clock at IOE register

Table 33. APEX 20K External Bidirectional Timing Parameters Note (1)

Symbol	Parameter	Conditions
$t_{INSUBIDIR}$	Setup time for bidirectional pins with global clock at same-row or same-column LE register	
$t_{INHBIDIR}$	Hold time for bidirectional pins with global clock at same-row or same-column LE register	
$t_{OUTCOBIDIR}$	Clock-to-output delay for bidirectional pins with global clock at IOE register	$C_1 = 10 \text{ pF}$
$t_{ZXBIDIR}$	Synchronous IOE output buffer disable delay	$C_1 = 10 \text{ pF}$
$t_{ZXBBIDIR}$	Synchronous IOE output buffer enable delay, slow slew rate = off	$C_1 = 10 \text{ pF}$

Table 41. EP20K200 f_{MAX} Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Units
	Min	Max	Min	Max	Min	Max	
t _{SU}	0.5		0.6		0.8		ns
t _H	0.7		0.8		1.0		ns
t _{CO}		0.3		0.4		0.5	ns
t _{LUT}		0.8		1.0		1.3	ns
t _{ESBRC}		1.7		2.1		2.4	ns
t _{ESBW}		5.7		6.9		8.1	ns
t _{ESBWESU}	3.3		3.9		4.6		ns
t _{ESBDATASU}	2.2		2.7		3.1		ns
t _{ESBDATAH}	0.6		0.8		0.9		ns
t _{ESBADDRS}	2.4		2.9		3.3		ns
t _{ESBDATACO1}		1.3		1.6		1.8	ns
t _{ESBDATACO2}		2.6		3.1		3.6	ns
t _{ESBDD}		2.5		3.3		3.6	ns
t _{PD}		2.5		3.0		3.6	ns
t _{PTERMSU}	2.3		2.7		3.2		ns
t _{PTERMCO}		1.5		1.8		2.1	ns
t _{F1-4}		0.5		0.6		0.7	ns
t _{F5-20}		1.6		1.7		1.8	ns
t _{F20+}		2.2		2.2		2.3	ns
t _{CH}	2.0		2.5		3.0		ns
t _{CL}	2.0		2.5		3.0		ns
t _{CLRP}	0.3		0.4		0.4		ns
t _{PREP}	0.4		0.5		0.5		ns
t _{ESBCH}	2.0		2.5		3.0		ns
t _{ESBCL}	2.0		2.5		3.0		ns
t _{ESBWP}	1.6		1.9		2.2		ns
t _{ESBRP}	1.0		1.3		1.4		ns

Table 46. EP20K200 External Bidirectional Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t _{INSUBIDIR} (1)	1.9		2.3		2.6		ns
t _{INHBIDIR} (1)	0.0		0.0		0.0		ns
t _{OUTCOBIDIR} (1)	2.0	4.6	2.0	5.6	2.0	6.8	ns
t _{XZBIDIR} (1)		5.0		5.9		6.9	ns
t _{ZXBIDIR} (1)		5.0		5.9		6.9	ns
t _{INSUBIDIR} (2)	1.1		1.2		—		ns
t _{INHBIDIR} (2)	0.0		0.0		—		ns
t _{OUTCOBIDIR} (2)	0.5	2.7	0.5	3.1	—	—	ns
t _{XZBIDIR} (2)		4.3		5.0		—	ns
t _{ZXBIDIR} (2)		4.3		5.0		—	ns

Table 47. EP20K400 External Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t _{INSU} (1)	1.4		1.8		2.0		ns
t _{INH} (1)	0.0		0.0		0.0		ns
t _{OUTCO} (1)	2.0	4.9	2.0	6.1	2.0	7.0	ns
t _{INSU} (2)	0.4		1.0		—		ns
t _{INH} (2)	0.0		0.0		—		ns
t _{OUTCO} (2)	0.5	3.1	0.5	4.1	—	—	ns

Table 48. EP20K400 External Bidirectional Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t _{INSUBIDIR} (1)	1.4		1.8		2.0		ns
t _{INHBIDIR} (1)	0.0		0.0		0.0		ns
t _{OUTCOBIDIR} (1)	2.0	4.9	2.0	6.1	2.0	7.0	ns
t _{XZBIDIR} (1)		7.3		8.9		10.3	ns
t _{ZXBIDIR} (1)		7.3		8.9		10.3	ns
t _{INSUBIDIR} (2)	0.5		1.0		—		ns
t _{INHBIDIR} (2)	0.0		0.0		—		ns
t _{OUTCOBIDIR} (2)	0.5	3.1	0.5	4.1	—	—	ns
t _{XZBIDIR} (2)		6.2		7.6		—	ns
t _{ZXBIDIR} (2)		6.2		7.6		—	ns

Table 60. EP20K60E External Bidirectional Timing Parameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t _{INSUBIDIR}	2.77		2.91		3.11		ns
t _{INHBDIR}	0.00		0.00		0.00		ns
t _{OUTCOBIDIR}	2.00	4.84	2.00	5.31	2.00	5.81	ns
t _{XZBIDIR}		6.47		7.44		8.65	ns
t _{ZXBIDIR}		6.47		7.44		8.65	ns
t _{INSUBIDIRPLL}	3.44		3.24		-		ns
t _{INHBDIRPLL}	0.00		0.00		-		ns
t _{OUTCOBIDIRPLL}	0.50	3.37	0.50	3.69	-	-	ns
t _{XZBIDIRPLL}		5.00		5.82		-	ns
t _{ZXBIDIRPLL}		5.00		5.82		-	ns

Tables 61 through 66 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K100E APEX 20KE devices.

Table 61. EP20K100E f_{MAX} LE Timing Microparameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t _{SU}	0.25		0.25		0.25		ns
t _H	0.25		0.25		0.25		ns
t _{CO}		0.28		0.28		0.34	ns
t _{LUT}		0.80		0.95		1.13	ns

Table 74. EP20K200E f_{MAX} ESB Timing Microparameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t _{ESBARC}		1.68		2.06		2.24	ns
t _{ESBSRC}		2.27		2.77		3.18	ns
t _{ESBAWC}		3.10		3.86		4.50	ns
t _{ESBSWC}		2.90		3.67		4.21	ns
t _{ESBWASU}	0.55		0.67		0.74		ns
t _{ESBWAH}	0.36		0.46		0.48		ns
t _{ESBWDSU}	0.69		0.83		0.95		ns
t _{ESBWDH}	0.36		0.46		0.48		ns
t _{ESBRASU}	1.61		1.90		2.09		ns
t _{ESBRAH}	0.00		0.00		0.01		ns
t _{ESBWESU}	1.42		1.71		2.01		ns
t _{ESBWEH}	0.00		0.00		0.00		ns
t _{ESBDATASU}	-0.06		-0.07		0.05		ns
t _{ESBDAZH}	0.13		0.13		0.13		ns
t _{ESBWADDRSU}	0.11		0.13		0.31		ns
t _{ESBRAADDRSU}	0.18		0.23		0.39		ns
t _{ESBDAZCO1}		1.09		1.35		1.51	ns
t _{ESBDAZCO2}		2.19		2.75		3.22	ns
t _{ESBDD}		2.75		3.41		4.03	ns
t _{PD}		1.58		1.97		2.33	ns
t _{PTERMSU}	1.00		1.22		1.51		ns
t _{PTERMCO}		1.10		1.37		1.09	ns

Table 75. EP20K200E f_{MAX} Routing Delays

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t _{F1-4}		0.25		0.27		0.29	ns
t _{F5-20}		1.02		1.20		1.41	ns
t _{F20+}		1.99		2.23		2.53	ns

Table 78. EP20K200E External Bidirectional Timing Parameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t _{INSUBIDIR}	2.81		3.19		3.54		ns
t _{INHBDIR}	0.00		0.00		0.00		ns
t _{OUTCOBIDIR}	2.00	5.12	2.00	5.62	2.00	6.11	ns
t _{XZBIDIR}		7.51		8.32		8.67	ns
t _{ZXBIDIR}		7.51		8.32		8.67	ns
t _{INSUBIDIRPLL}	3.30		3.64		-		ns
t _{INHBDIRPLL}	0.00		0.00		-		ns
t _{OUTCOBIDIRPLL}	0.50	3.01	0.50	3.36	-	-	ns
t _{XZBIDIRPLL}		5.40		6.05		-	ns
t _{ZXBIDIRPLL}		5.40		6.05		-	ns

Tables 79 through 84 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K300E APEX 20KE devices.

Table 79. EP20K300E f_{MAX} LE Timing Microparameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t _{SU}	0.16		0.17		0.18		ns
t _H	0.31		0.33		0.38		ns
t _{CO}		0.28		0.38		0.51	ns
t _{LUT}		0.79		1.07		1.43	ns

Tables 97 through 102 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K1000E APEX 20KE devices.

Table 97. EP20K1000E f_{MAX} LE Timing Microparameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t _{SU}	0.25		0.25		0.25		ns
t _H	0.25		0.25		0.25		ns
t _{CO}		0.28		0.32		0.33	ns
t _{LUT}		0.80		0.95		1.13	ns

Table 98. EP20K1000E f_{MAX} ESB Timing Microparameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t _{ESBARC}		1.78		2.02		1.95	ns
t _{ESBSRC}		2.52		2.91		3.14	ns
t _{ESBAWC}		3.52		4.11		4.40	ns
t _{ESBSWC}		3.23		3.84		4.16	ns
t _{ESBWASU}	0.62		0.67		0.61		ns
t _{ESBWAH}	0.41		0.55		0.55		ns
t _{ESBWDSU}	0.77		0.79		0.81		ns
t _{ESBWDH}	0.41		0.55		0.55		ns
t _{ESBRASU}	1.74		1.92		1.85		ns
t _{ESBRAH}	0.00		0.01		0.23		ns
t _{ESBWESU}	2.07		2.28		2.41		ns
t _{ESBWEH}	0.00		0.00		0.00		ns
t _{ESBDATASU}	0.25		0.27		0.29		ns
t _{ESBDATAH}	0.13		0.13		0.13		ns
t _{ESBWADDRSU}	0.11		0.04		0.11		ns
t _{ESBRADDRSU}	0.14		0.11		0.16		ns
t _{ESBDAACO1}		1.29		1.50		1.63	ns
t _{ESBDAACO2}		2.55		2.99		3.22	ns
t _{ESBDD}		3.12		3.57		3.85	ns
t _{PD}		1.84		2.13		2.32	ns
t _{PTERMSU}	1.08		1.19		1.32		ns
t _{PTERMCO}		1.31		1.53		1.66	ns

Table 99. EP20K1000E f_{MAX} Routing Delays

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{F1-4}		0.27		0.27		0.27	ns
t_{F5-20}		1.45		1.63		1.75	ns
t_{F20+}		4.15		4.33		4.97	ns

Table 100. EP20K1000E Minimum Pulse Width Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{CH}	1.25		1.43		1.67		ns
t_{CL}	1.25		1.43		1.67		ns
t_{CLRP}	0.20		0.20		0.20		ns
t_{PREP}	0.20		0.20		0.20		ns
t_{ESBCH}	1.25		1.43		1.67		ns
t_{ESBCL}	1.25		1.43		1.67		ns
t_{ESBWP}	1.28		1.51		1.65		ns
t_{ESBRP}	1.11		1.29		1.41		ns

Table 101. EP20K1000E External Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.70		2.84		2.97		ns
t_{INH}	0.00		0.00		0.00		ns
t_{OUTCO}	2.00	5.75	2.00	6.33	2.00	6.90	ns
$t_{INSUPLL}$	1.64		2.09		-		ns
t_{INHPLL}	0.00		0.00		-		ns
$t_{OUTCOPLL}$	0.50	2.25	0.50	2.99	-	-	ns

Table 106. EP20K1500E Minimum Pulse Width Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t _{CH}	1.25		1.43		1.67		ns
t _{CL}	1.25		1.43		1.67		ns
t _{CLRP}	0.20		0.20		0.20		ns
t _{PREP}	0.20		0.20		0.20		ns
t _{ESBCH}	1.25		1.43		1.67		ns
t _{ESBCL}	1.25		1.43		1.67		ns
t _{ESBWP}	1.28		1.51		1.65		ns
t _{ESBRP}	1.11		1.29		1.41		ns

Table 107. EP20K1500E External Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t _{INSU}	3.09		3.30		3.58		ns
t _{INH}	0.00		0.00		0.00		ns
t _{OUTCO}	2.00	6.18	2.00	6.81	2.00	7.36	ns
t _{INSUPLL}	1.94		2.08		-		ns
t _{INHPLL}	0.00		0.00		-		ns
t _{OUTCOPLL}	0.50	2.67	0.50	2.99	-	-	ns